## N-Channel 100-V (D-S) MOSFET

# **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

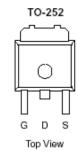
<b>Typical</b>	App	lications:
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- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I□ (A)	
100	12 @ V <sub>GS</sub> = 10V	52.8	
	$17 @ V_{GS} = 6.5V$	44.3	







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage		$V_{DS}$	100	V	
Gate-Source Voltage		$V_{GS}$	±20	\ \ \ \ \ \	
Continuous Drain Current a	T <sub>C</sub> =25°C	$I_D$	52.8	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	240	Α	
Continuous Source Current (Diode Conduction) a			50	Α	
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	$P_{D}$	50	W	
Operating Junction and Storage Temperature Range	·	$T_J, T_{stg}$	-55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	3	C/VV		

1

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

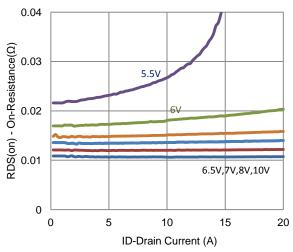
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Gurrent	I <sub>DSS</sub>	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	79.2			Α	
Drain-Source On-Resistance <sup>a</sup>	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			12	mΩ	
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = 6.5 \text{ V}, I_D = 18 \text{ A}$			17	11122	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = 50 \text{ V}, I_{D} = 20 \text{ A}$		35		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 25 \text{ A}, V_{GS} = 0 \text{ V}$		0.9		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = 50 \text{ V}, V_{GS} = 6.5 \text{ V},$		19			
Gate-Source Charge	$Q_{gs}$	$I_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0.3 \text{ V},$ $I_{D} = 2 \text{ A}$		6.2		nC	
Gate-Drain Charge	$Q_gd$	10 - 2 A		9.2			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 50 \text{ V}, R_{L} = 25 \Omega,$		12			
Rise Time	t <sub>r</sub>	$V_{DS} = 50 \text{ V}, R_L - 25 \Omega,$ $I_D = 2 \text{ A},$		13		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		25		ns	
Fall Time	t <sub>f</sub>	V GEN = 10 V, 1 (GEN = 0.22		29			
Input Capacitance	C <sub>iss</sub>	_		1160			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		206		pF	
Reverse Transfer Capacitance	$C_{rss}$			14			

#### **Notes**

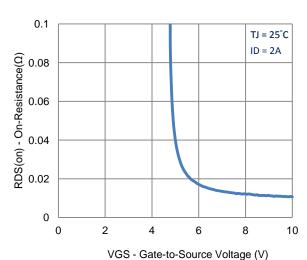
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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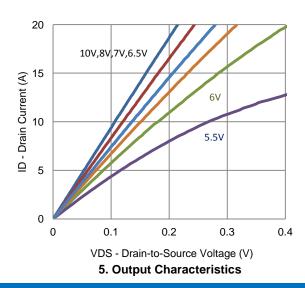
### **Typical Electrical Characteristics**

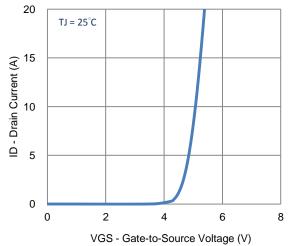


#### 1. On-Resistance vs. Drain Current

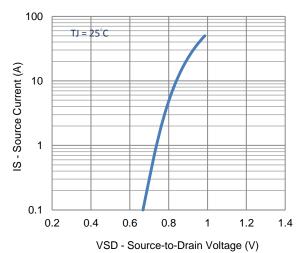


3. On-Resistance vs. Gate-to-Source Voltage

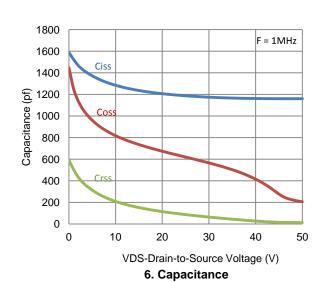




2. Transfer Characteristics



4. Drain-to-Source Forward Voltage



### **Typical Electrical Characteristics**

2.5

2

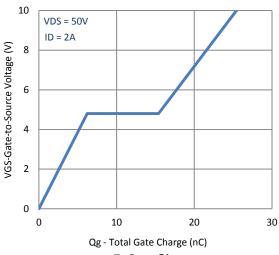
1.5

0.5

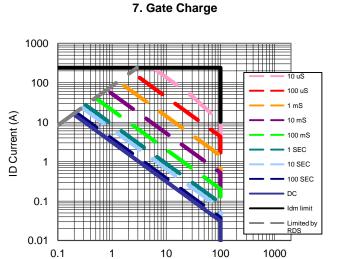
-50

-25

 $RDS(on) - On-Resistance(\Omega) \\ (Normalized)$ 

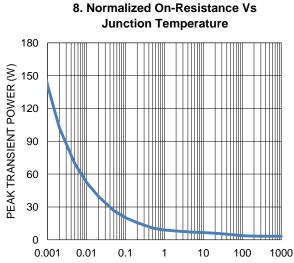






VDS Drain to Source Voltage (V)

9. Safe Operating Area



0

25

50

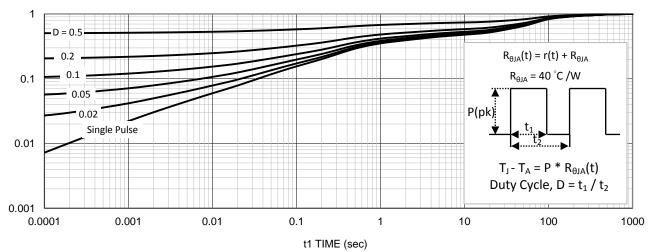
75

100

125 150

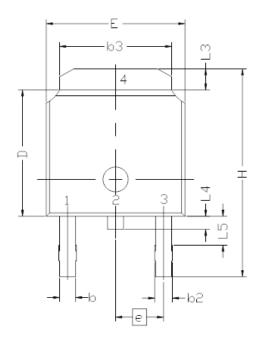
t1 TIME (SEC)

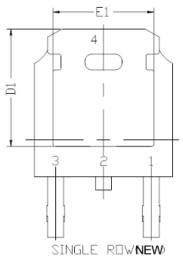
10. Single Pulse Maximum Power Dissipation

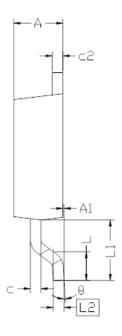


11. Normalized Thermal Transient Junction to Ambient

## **Package Information**







OVALDEL	DIMENS:	IDNAL F	REQMTS
SYMBOL	MIN	NDM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2	.743 RI	ĒF
	0.	.508 BS	_
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6,223
Н	9.40	10.00	10.40
b	0.64	0.76	0,88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
е		286 BS	
Α	2,20	2.30	2,38
A1	0		0.127
С	0.45	0.50	0.60
c2	0.45	0.50	0,58
D1	5,30		
E1	4.40		
θ	0*		10°

#### Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.